

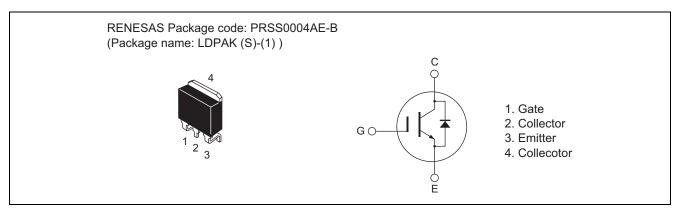
RJH60D1DPE

Silicon N Channel IGBT Application: Inverter

Features

- High breakdown-voltage
- Low on-voltage
- Built-in diode

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$ Item Symbol Ratings Unit V Collector to emitter voltage / diode reverse voltage V_{CES} / V_R 600 V ±30 Gate to emitter voltage V_{GES} Tc = 25°C Collector current 16 Α lc Tc = 100°C Α 8 lc ic(peak) Note1 Collector peak current 32 А Collector to emitter diode forward current \mathbf{i}_{DF} 8 А i_{DF}(peak)^{Note1} 32 Collector to Emitter diode forward peak current А P_C^{Note2} Collector dissipation 70 W θj-c^{Note2} 1.79 °C/W Junction to case thermal impedance Junction temperature Тj 150 °C Storage temperature Tstg -55 to +150 °C

Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

2. Value at Tc = 25°C

REJ03G1840-0100 Rev.1.00

Oct 14, 2009

Preliminary

Electrical Characteristics

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						$(Ta = 25^{\circ}C)$
ltem	Symbol	Min	Тур	Max	Unit	Test Conditions
Zero gate voltage collector current / Diode reverse current	I _{CES} / I _R	_	—	100	μA	V _{CE} = 600 V, V _{GE} = 0
Gate to emitter leak current	I _{GES}	_	_	±1	μA	$V_{GE} = \pm 30 \text{ V}, \text{ V}_{CE} = 0$
Gate to emitter cutoff voltage	V _{GE(off)}	4.0	_	6.0	V	V _{CE} = 10 V, I _C = 1 mA
Collector to emitter saturation voltage	V _{CE(sat)}	_	1.8	2.2	V	I _C = 8 A, V _{GE} = 15 V ^{Note3}
	V _{CE(sat)}	_	2.3	—	V	I_{C} = 16 A, V_{GE} = 15 V ^{Note3}
Input capacitance	Cies	_	290	—	pF	V _{CE} = 25 V
Output capacitance	Coes	_	25	_	pF	V _{GE} = 0 f = 1 MHz
Reveres transfer capacitance	Cres	_	7.5	—	pF	
Total gate charge	Qg	_	12.0	—	nC	V _{GE} = 15 V V _{CE} = 300 V I _C = 8 A
Gate to emitter charge	Qge		2.0		nC	
Gate to collector charge	Qgc	_	6.0		nC	
Switching time	t _{d(on)}		25		ns	I _C = 8 A
	tr	_	35		ns	R _L = 37.5 Ω
	t _{d(off)}	_	40	—	ns	V _{GE} = 15 V
	t _f	_	100	—	ns	Rg = 5 Ω

FRD forward voltage	V_{F}	_	1.8	2.3	V	I _F = 8 A ^{Note3}
FRD reverse recovery time	trr	—	100	_	ns	I _F = 8 A
						di _F /dt = 100 A/µs

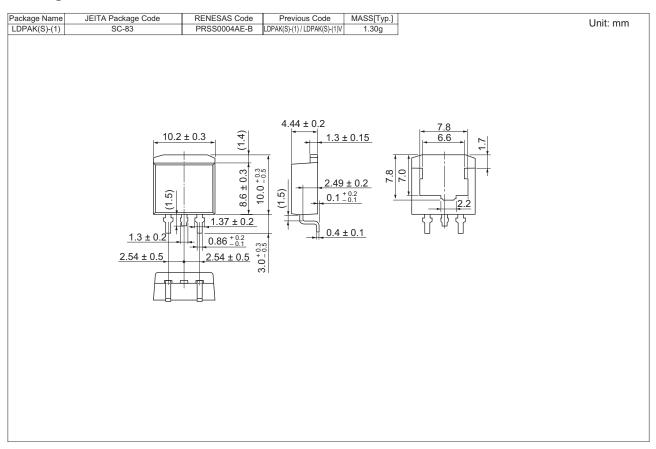
Notes: 3. Pulse test.

4. Under development. - The specification potentially be changed without notice.

Preliminary

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Package Dimension



Ordering Information

Part No.	Quantity	Shipping Container
RJH60D1DPE-00-J3	1000 pcs	Taping

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